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3.3-V FULL-DUPLEX RS-485 DRIVERS AND RECEIVERS

FEATURES

- Controlled Baseline
 - One Assembly Site
 - One Test Site
 - One Fabrication Site
- Extended Temperature Performance of −55°C to 125°C
- Enhanced Diminishing Manufacturing Sources (DMS) Support
- Enhanced Product-Change Notification
- Qualification Pedigree⁽¹⁾
- Available in the Texas Instruments
 NanoStar™ and NanoFree™ Packages
- 1/8 Unit-Load Option Available (up to 256 Nodes on the Bus)
- Bus-Pin ESD Protection Exceeds 15-kV HBM
- Optional Driver Output Transition Times for Signaling Rates⁽²⁾ of 1 Mbps, 5 Mbps, and 25 Mbps
- Low-Current Standby Mode: <1 μA
- Glitch-Free Power-Up and Power-Down Protection for Hot-Plugging Applications
- 5-V-Tolerant Inputs
- Bus Idle, Open, and Short-Circuit Fail Safe
- Driver Current Limiting and Thermal Shutdown
- Meet or Exceed the Requirements of ANSI TIA/EIA-485-A and RS-422 Compatible
- (1) Component qualification in accordance with JEDEC and industry standards to ensure reliable operation over an extended temperature range. This includes, but is not limited to, Highly Accelerated Stress Test (HAST) or biased 85/85, temperature cycle, autoclave or unbiased HAST, electromigration, bond intermetallic life, and mold compound life. Such qualification testing should not be viewed as justifying use of this component beyond specified performance and environmental limits.
- (2) The signaling rate of a line is the number of voltage transitions that are made per second expressed in the units bps (bits per second).

APPLICATIONS

- Utility Meters
- DTE/DCE Interfaces
- Industrial, Process, and Building Automation
- Point-of-Sale (POS) Terminals and Networks

DESCRIPTION

The SN65HVD3x devices are 3-state differential line drivers and differential-input line receivers that operate with 3.3-V power supply.

Each driver and receiver has separate input and output pins for full-duplex bus communication designs. They are designed for balanced transmission lines and interoperation with ANSI TIA/EIA-485A, TIA/EIA-422-B, ITU-T v.11, and ISO 8482:1993 standard-compliant devices.

The SN65HVD30, SN65HVD31, SN65HVD32, SN65HVD36, and SN65HVD37 are fully enabled with no external enabling pins. The SN65HVD36 and SN65HVD37 implement receiver equalization technology for improved performance in long distance applications.

The SN65HVD33, SN65HVD34, SN65HVD35, SN65HVD38, and SN65HVD39 have active-high driver enables and active-low receiver enables. A low (less than 1 μ A) standby current can be achieved by disabling both the driver and receiver. The SN65HVD38 and SN65HVD39 implement receiver equalization technology for improved performance in long distance applications.

The SN65HVD36 and SN65HVD38 implement receiver equalization technology for improved jitter performance on differential bus applications with data rates up to 20 Mbps at cable lengths up to 160 meters.

The SN65HVD37 and SN65HVD39 implement receiver equalization technology for improved jitter performance on differential bus applications with data rates in the range of 1 Mbps to 5 Mbps at cable lengths up to 1000 meters.

All devices are characterized for operation from –55°C to 125°C.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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IMPROVED REPLACEMENT FOR:

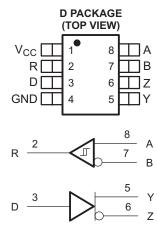
Part Number	Replace With	
xxx3491 xxx3490	SN65HVD33: SN65HVD30:	Better ESD protection (15 kV vs 2 kV or not specified), higher signaling rate (25 Mbps vs 20 Mbps), fractional unit load (64 nodes vs 32)
MAX3491E MAX3490E	SN65HVD33: SN65HVD30:	Higher signaling rate (25 Mbps vs 12 Mbps), fractional unit load (64 nodes vs 32)
MAX3076E MAX3077E	SN65HVD33: SN65HVD30:	Higher signaling rate (25 Mbps vs 16 Mbps), lower standby current (1 μA vs 10 μA)
MAX3073E MAX3074E	SN65HVD34: SN65HVD31:	Higher signaling rate (5 Mbps vs 500 kbps), lower standby current (1 μA vs 10 μA)
MAX3070E MAX3071E	SN65HVD35: SN65HVD32:	Higher signaling rate (1 Mbps vs 250 kbps), lower standby current (1 μA vs 10 μA)



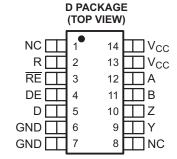
This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

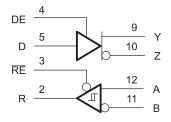
SN65HVD30, SN65HVD31, SN65HVD32, SN65HVD36, SN65HVD37



SN65HVD33, SN65HVD34, SN65HVD35, SN65HVD38, SN65HVD39



NC - No internal connection



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AVAILABLE OPTIONS(1)

BASE PART NUMBER	SIGNALING RATE	UNIT LOADS	RECEIVER EQUALIZATION	ENABLES	SOIC MARKING
SN65HVD30MDREP	25 Mbps		No	No	HVD30EP
SN65HVD31MDREP ⁽²⁾	5 Mbps	1/8	No	No	PREVIEW
SN65HVD32MDREP ⁽²⁾	1 Mbps	1/8	No	No	PREVIEW
SN65HVD33MDREP	25 Mbps		No	Yes	HVD33EP
SN65HVD34MDREP ⁽²⁾	5 Mbps	1/8	No	Yes	PREVIEW
SN65HVD35MDREP ⁽²⁾	1 Mbps	1/8	No	Yes	PREVIEW
SN65HVD36MDREP ⁽²⁾	25 Mbps		Yes	No	PREVIEW
SN65HVD37MDREP ⁽²⁾	5 Mbps	1/8	Yes	No	PREVIEW
SN65HVD38MDREP ⁽²⁾	25 Mbps		Yes	Yes	PREVIEW
SN65HVD39MDREP ⁽²⁾	5 Mbps	1/8	Yes	Yes	PREVIEW

⁽¹⁾ For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI Web site at www.ti.com.

Absolute Maximum Ratings (1)(2)

over operating free-air temperature range (unless otherwise noted)

		UNIT
V _{CC}	Supply voltage range	–0.3 V to 6 V
V _(A) , V _(B) , V _(Y) , V _(Z)	Voltage range at any bus terminal (A, B, Y, Z)	–9 V to 14 V
V _(TRANS)	Voltage input, transient pulse through 100 Ω (see Figure 12) (A, B, Y, Z) ⁽³⁾	–50 V to 50 V
V _I	Input voltage range (D, DE, RE)	–0.5 V to 7 V
P _{D(cont)}	Continuous total power dissipation	Internally limited ⁽⁴⁾
Io	Output current (receiver output only, R)	11 mA
T _J	Junction temperature	165°C
T _{STG}	Storage temperature range	–65°C to 150°C

⁽¹⁾ Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

⁽²⁾ Product Preview

⁽²⁾ All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.

⁽³⁾ This tests survivability only and the output state of the receiver is not specified.

⁽⁴⁾ The thermal shutdown protection circuit internally limits the continuous total power dissipation. Thermal shutdown typically occurs when the junction temperature reaches 165°C.

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Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

					MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage				3		3.6	V
V _I or V _{IC}	Voltage at any bus	s terminal (se	eparat	tely or common mode)	-7 ⁽¹⁾		12	V
	'HVD30, 'HVD33, 'HVD36, 'HVD38						25	
1/t _{UI}	Signaling rate	'HVD31, 'H\	VD34	, 'HVD37, 'HVD39			5	Mbps
		'HVD32, 'H\	VD35				1	
R _L	Differential load re	sistance			54	60		Ω
V _{IH}	High-level input vo	oltage	D,	DE, RE	2		V_{CC}	V
V _{IL}	Low-level input vo	Itage	D,	DE, RE	0		8.0	V
V _{ID}	Differential input v	oltage			-12		12	V
	I limb lavel avitovit		Dri	iver	-60			Λ
I _{OH}	High-level output of	High-level output current		eceiver	-8			mA
	Low-level output current		Dri	iver			60	Λ
I _{OL}			Re	eceiver			8	mA
T _A	Ambient still-air te	mperature			-55		125 ⁽²⁾	°C

⁽¹⁾ The algebraic convention, in which the least positive (most negative) limit is designated as minimum, is used in this data sheet.

Electrostatic Discharge Protection

PARAMETER	TEST CONDITIONS	TYP ⁽¹⁾	UNIT
Human-Body Model	Bus terminals and GND	±16	
Human-Body Model (2)	All pins	±4	kV
Charged-Device Model (3)	All pins	±1	

⁽¹⁾ All typical values at 25°C with 3.3-V supply

Long-term high-temperature storage and/or extended use at maximum recommended operating conditions may result in a reduction of overall device life. See http://www.ti.com/ep_quality for additional information on enhanced plastic packaging.

 ⁽²⁾ Tested in accordance with JEDEC Standard 22, Test Method A114-A
 (3) Tested in accordance with JEDEC Standard 22, Test Method C101

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Driver Electrical Characteristics

	PARAMET	ER	TEST CONDITIO	NS	MIN	TYP ⁽¹⁾	MAX	UNIT
$V_{I(K)}$	Input clamp volta	ge	$I_{I} = -18 \text{ mA}$		-1.5			V
			I _O = 0	2.3		V _{CC} + 0.1		
$ V_{OD(SS)} $	Steady-state diffe	rential output voltage	$R_L = 54 \Omega$, See Figure 1 (RS-4	485)	1.5	2		V
()			$R_L = 100 \Omega$, See Figure 1 (RS	5-422)	2	2.3		
			$V_{\text{test}} = -7 \text{ V to } 12 \text{ V, See Figu}$	re 2	1.5			
$\Delta V_{OD(SS)} $	Change in magni differential output states	tude of steady-state voltage between	R_L = 54 Ω , See Figure 1 and F	Figure 2	-0.2		0.2	V
V _{OD(RING)}	Differential outpu and undershoot	t voltage overshoot	$R_L = 54 \Omega$, $C_L = 50 pF$, See Figure 3	igure 5 and			10%(2)	V
	Peak-to-peak 'HVD30, 'HVD33, 'HVD38		See Figure 4			0.5		
V _{OC(PP)} common-mode output voltage 'HVD31, 'HVD34, 'HVD37, 'HVD39, 'HVD32, 'HVD35		'HVD37, 'HVD39,				0.25		V
V _{OC(SS)}	Steady-state com voltage	mon-mode output	See Figure 4		1.6		2.3	V
$\Delta V_{OC(SS)}$	Change in steady common-mode o		See Figure 4		-0.05		0.05	V
		'HVD30, 'HVD31, 'HVD32, 'HVD36,	$V_{CC} = 0 \text{ V}, V_Z \text{ or } V_Y = 12 \text{ V},$ Other input at 0 V				90	
$I_{Z(Z)}$ or	High-impedance	'HVD37	$V_{CC} = 0 \text{ V}, V_{Z} \text{ or } V_{Y} = -7 \text{ V},$ Other input at 0 V		-10			4
$I_{Y(Z)}^{-(-)}$	state output current	'HVD33, 'HVD34, 'HVD35, 'HVD38,	$V_{CC} = 3 \text{ V or } 0 \text{ V, DE} = 0 \text{ V,} $ $V_{Z} \text{ or } V_{Y} = 12 \text{ V}$	Other input			90	μΑ
		'HVD39	$V_{CC} = 3 \text{ V or } 0 \text{ V, DE} = 0 \text{ V,} $ $V_{Z} \text{ or } V_{Y} = -7 \text{ V}$	at 0 V	-10			
I _{Z(S)} or	or Short-circuit output current		V_Z or $V_Y = -7 V$	Other input		±250		mA
I _{Y(S)}	Short-circuit outp	ut Current	V_Z or $V_Y = 12 \text{ V}$ at 0 V			1200		ША
l _l	Input current	D, DE			0		100	μΑ
$C_{(OD)}$	Differential outpu	t capacitance	$V_{OD} = 0.4 \sin (4E6\pi t) + 0.5 V,$	DE at 0 V		16		pF

⁽¹⁾ All typical values at 25°C with 3.3-V supply

^{(2) 10%} of the peak-to-peak differential output voltage swing, per TIA/EIA-485

SN65HVD30-EP, SN65HVD31-EP, SN65HVD32-EP, SN65HVD33-EP, SN65HVD34-EP SN65HVD35-EP, SN65HVD36-EP, SN65HVD37-EP, SN65HVD38-EP, SN65HVD39-EP



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Driver Switching Characteristics

	PARAM	IETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT	
		'HVD30, 'HVD33, 'HVD36, 'HVD38		4	10	23		
t _{PLH}	Propagation delay time, low- to high-level output	'HVD31, 'HVD34, 'HVD37, 'HVD39		25	38	65	ns	
	low to riight level output	'HVD32, 'HVD35		120	175	305		
		'HVD30, 'HVD33, 'HVD36, 'HVD38		4	9	23		
t_{PHL}	Propagation delay time, high- to low-level output	'HVD31, 'HVD34, 'HVD37, 'HVD39		25	38	65	ns	
	riigii to low level output	'HVD32, 'HVD35		120	175	305		
		'HVD30, 'HVD33, 'HVD36, 'HVD38		2.5	5	18		
t _r	Differential output signal rise time	'HVD31, 'HVD34, 'HVD37, 'HVD39	$R_L = 54 \Omega$, $C_L = 50 pF$, See Figure 5	20	37	60	ns	
	noe une	'HVD32, 'HVD35	J Coc riguio o	120	185	300		
		'HVD30, 'HVD33, 'HVD36, 'HVD38		2.5	5	18		
t _f	Differential output signal fall time	'HVD31, 'HVD34, 'HVD37, 'HVD39		20	35	60	ns	
		'HVD32, 'HVD35		120	180	300		
		'HVD30, 'HVD33, 'HVD36, 'HVD38			0.6		ns	
t _{sk(p)}	Pulse skew (t _{PHL} - t _{PLH})	'HVD31, 'HVD34, 'HVD37, 'HVD39	-		2.0			
		'HVD32, 'HVD35			5.1			
	Propagation delay time,	'HVD33, 'HVD38	$R_L = 110 \Omega$, \overline{RE} at 0 V,			45	45	
t _{PZH1}	high-impedance to high-level	'HVD34, 'HVD39				235	ns	
	output	'HVD35	D = 3 V and S1 = Y, or S1 = Y			490	490	
	Propagation delay time,	'HVD33, 'HVD38	D = 0 V and S1 = Z,			25		
t_{PHZ}	high-level to high-impedance	'HVD34, 'HVD39	See Figure 6			65	ns	
	output	'HVD35				165		
	Propagation delay time,	'HVD33, 'HVD38				35		
t _{PZL1}	high-impedance to low-level	'HVD34, 'HVD39	B = 110 O DE at 0 V			190	ns	
	output	'HVD35	$R_L = 110 \Omega$, \overline{RE} at 0 V, $D = 3 V$ and $S1 = Z$, or			490		
	Propagation delay time,	'HVD33, 'HVD38	D = 0 V and S1 = Y,			30		
t_{PLZ}	low-level to high-impedance	'HVD34, 'HVD39	See Figure 7			120	ns	
	output	'HVD35				290		
		'HVD30	$R_L = 110 \Omega$, \overline{RE} at 3 V,			4000		
t _{PZH2}	Propagation delay time, standby to high-level output	'HVD33	D = 3 V and S1 = Y, or D = 0 V and S1 = Z, See Figure 6			5000	ns	
		'HVD30	$R_L = 110 \Omega$, \overline{RE} at 3 V,			4000		
t _{PZL2}	Propagation delay time, standby to low-level output	'HVD33	D = 3 V and S1 = Z, or D = 0 V and S1 = Y, See Figure 7			5000	ns	

⁽¹⁾ All typical values at 25°C with 3.3-V supply

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Receiver Electrical Characteristics

	PARAME	ΓER	TEST CONDITIO	NS	MIN	TYP ⁽¹⁾	MAX	UNIT		
V _{IT+}	Positive-going different voltage	ial input threshold	$I_O = -8 \text{ mA}$	$I_O = -8 \text{ mA}$		$I_{O} = -8 \text{ mA}$			-0.02	V
	Negative-going	'HVD30			-0.15					
V_{IT-}	differential input threshold voltage	'HVD33	I _O = 8 mA		-0.2			V		
V _{hys}	Hysteresis voltage (V _{IT}	- ₊ - V _{IT-})				50		mV		
V _{IK}	Enable-input clamp vol	tage	$I_{I} = -18 \text{ mA}$		-1.5			V		
Vo	Output voltage		$V_{ID} = 200 \text{ mV}, I_O = -8 \text{ mA}, Se$	ee Figure 8	2.4			V		
۷0	Output voltage		$V_{ID} = -200 \text{ mV}, I_{O} = 8 \text{ mA}, Se$	ee Figure 8			0.4	v		
$I_{O(Z)}$	High-impedance-state	output current	$V_O = 0$ or V_{CC} , \overline{RE} at V_{CC}		-1		1	μΑ		
			V_A or $V_B = 12 V$			0.05	0.1			
		'HVD31, 'HVD32, 'HVD34, 'HVD35,	V_A or $V_B = 12 \text{ V}$, $V_{CC} = 0 \text{ V}$	Other input		0.06	0.1			
		'HVD37, 'HVD39	V_A or $V_B = -7 \text{ V}$	at 0 V	-0.10	-0.04				
I _A or	Bus input current		V_A or $V_B = -7 V$, $V_{CC} = 0 V$		-0.10	-0.03		mA		
I_B	Dus input current		V_A or $V_B = 12 V$			0.20	0.35	ША		
		'HVD30, 'HVD33,	V_A or $V_B = 12 \text{ V}$, $V_{CC} = 0 \text{ V}$	Other input at 0 V		0.24	0.4			
		'HVD36, 'HVD38	V_A or $V_B = -7 V$		-0.35	-0.18				
			V_A or $V_B = -7 V$, $V_{CC} = 0 V$		-0.25	-0.13				
I _{IH}	Input current, RE		$V_{IH} = 0.8 \text{ V or } 2 \text{ V}$		-60			μΑ		
C_{ID}	Differential input capac	itance	$V_{ID} = 0.4 \sin (4E6\pi t) + 0.5 V$,	DE at 0 V		15		pF		
Suppl	y Current									
		'HVD30					2.1			
		'HVD31, 'HVD32	D at 0 V or V _{CC} and no load				6.4			
		'HVD36, 'HVD37					7.9	mA		
		'HVD33	RE at 0 V, D at 0 V or V _{CC} , D	E at 0 V,			1.8	mA		
		'HVD34, 'HVD35	No load (receiver enabled an	d driver			2.2			
		'HVD38, 'HVD39	disabled)				3.8			
		'HVD33, 'HVD34, 'HVD35, 'HVD38, 'HVD39		RE at V _{CC} , D at V _{CC} , DE at 0 V, No load (receiver disabled and driver disabled)		0.022	1.5	μΑ		
I_{CC}	Supply current 'HVD33					2.1				
		'HVD34, 'HVD35	RE at 0 V, D at 0 V or V _{CC} , D	E at V _{CC} ,			6.5			
		'HVD38	No load (receiver enabled and driver enabled)				3.5	mA		
		'HVD39					8			
		'HVD33 'HVD34, 'HVD35 RE at V _{CC} , D at 0 V or V _{CC} , DE at V _{CC}				1.8				
						6.2				
	'HVD38 No load (receiver disabled and driver enabled)				2.5					
		'HVD39	onabiou)				7			

⁽¹⁾ All typical values at 25°C with 3.3-V supply

SN65HVD30-EP, SN65HVD31-EP, SN65HVD32-EP, SN65HVD33-EP, SN65HVD34-EP SN65HVD35-EP, SN65HVD36-EP, SN65HVD37-EP, SN65HVD38-EP, SN65HVD39-EP



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Receiver Switching Characteristics

	PARAMETER			TEST CONDITIONS			MAX	UNIT	
	Dropogation delay time	'HVD30, 'HVD33, 'HVD36, 'HVD38			26	60			
t _{PLH}	Propagation delay time, low- to high-level output	'HVD31, 'HVD32, 'HVD34, 'HVD35, 'HVD37, 'HVD39				47	70	ns	
	Dranagation dalay time	'HVD30, 'HVD33, 'HVD36, 'HVD38				29	60		
t _{PHL}	Propagation delay time, high- to low-level output	'HVD31, 'HVD32, 'HVD34, 'HVD35, 'HVD37, 'HVD39	V _{ID} = -1.5 V	to 1.5 V		49	70	ns	
t _{sk(p)}	Pulse skew (t _{PHL} – t _{PLH})	'HVD30, 'HVD33, 'HVD36, 'HVD37, 'HVD38, 'HVD39		_{ID} = -1.5 V to 1.5 V, _L = 15 pF, See Figure 9			12	ns	
(-)		'HVD31, 'HVD34, 'HVD32, 'HVD35					10		
	Output signal rise time	'HVD30					10	20	
t _r	Output signal rise time	'HVD33					18	ns	
t _f	Output signal fall time						12.5	ns	
t_{PHZ}	Output disable time from high	h level	DE at 3 V				20	ns	
t _{PZH1}	Output enable time to high le	evel	DE at 3 V	$C_{L} = 15 \text{ pF},$			20	ns	
	Propagation delay time,	'HVD30	DE at 0 V	See Figure 10			4000	20	
t _{PZH2}	standby to high-level output	'HVD33	DE al U V	V			5000	ns	
t _{PLZ}	Output disable time from low	DE at 3 V					20	ns	
t _{PZL1}	Output enable time to low lev			$C_1 = 15 pF,$			20	ns	
	Propagation delay time.	Propagation delay time,	'HVD30	DE -+ 0.1/	See Figure 11			4000	
t _{PZL2}	standby to low-level output	'HVD33	DE at 0 V				5000	ns	

⁽¹⁾ All typical values 25°C with 3.3-V supply



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Receiver Equalization Characteristics

over recommended operating conditions (unless otherwise noted)

ı	PARAMETER	TEST CONDIT	TIONS		DEVICE	MIN TYP ⁽¹⁾	MAX	UNIT
				0 m	'HVD36, 'HVD38	PREVIEW		
				100 m	'HVD33 ⁽²⁾	PREVIEW		
				100 111	'HVD36, 'HVD38	PREVIEW		
			25 Mbps	150 m	'HVD33 ⁽²⁾	PREVIEW		
				150 111	'HVD36, 'HVD38	PREVIEW		
			200 m	'HVD33 ⁽²⁾	PREVIEW			
				200 m	'HVD36, 'HVD38	PREVIEW		
			200 m 10 Mbps 250 m 300 m	'HVD33 ⁽²⁾	PREVIEW			
		Pseudo-random NRZ code with a bit pattern length of		200 111	'HVD36, 'HVD38	PREVIEW		ns
				10 Mbps 250 m	'HVD33 ⁽²⁾	PREVIEW		
t _{j(pp)}	Peak-to-peak eye-pattern jitter				'HVD36, 'HVD38	PREVIEW		
	oyo panom jinor	2 ¹⁶ – 1, Belden 3105A cable		200 m	'HVD33 ⁽²⁾	PREVIEW		
				300 111	'HVD36, 'HVD38	PREVIEW		
			E Mhno	500 m	'HVD34 ⁽²⁾	PREVIEW		
			5 Mbps	500 m	'HVD37, 'HVD39	PREVIEW		
					'HVD33 ⁽²⁾	PREVIEW		
			O Mha	500	'HVD34 ⁽²⁾	PREVIEW		
			3 Mbps	500 m	'HVD36, 'HVD38	PREVIEW		
					'HVD37, 'HVD39	PREVIEW		
			1 Mbno	1000 m	'HVD34 ⁽²⁾	PREVIEW		
			1 Mbps	1000 m	'HVD37, 'HVD39	PREVIEW		

Device Power Dissipation – PD

DEVICE	TEST CONDITIONS	MIN M	IAX	UNIT
'HVD30, 'HVD36 (25 Mbps)	$R_L = 60 \Omega$, $C_L = 50 pF$, Input to D a 50% duty cycle square wave at indicated signaling rate, $T_A = 85^{\circ}C$		197	
'HVD31, 'HVD37 (5 Mbps)			213	mW
'HVD32 (1 Mbps)	imput to B a 50% addy by the equation was at maleated eightning rate, 14 = 50 0	1	193	
'HVD33, 'HVD38 (25 Mbps)		1	197	
'HVD34, 'HVD39 (5 Mbps)	$R_L = 60 \Omega$, $C_L = 50$ pF, DE at V_{CC} , \overline{RE} at 0 V, nput to D a 50% duty cycle square wave at indicated signaling rate, $T_A = 85^{\circ}C$		193	mW
'HVD35 (1 Mbps)	par. 10 2 a 3070 aas, 5,510 squa.10a.10 at indibatod signaling rato, 1 _A = 00 0	2	248	

⁽¹⁾ All typical values are at $V_{CC} = 5$ V and temperature = 25°C. (2) The SN65HVD33 and the SN65HVD34 do not have receiver equalization, but are specified for comparison.



PARAMETER MEASUREMENT INFORMATION

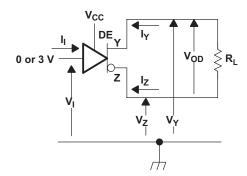


Figure 1. Driver V_{OD} Test Circuit and Voltage and Current Definitions

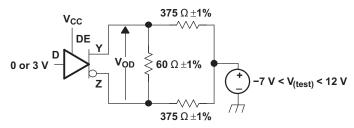


Figure 2. Driver V_{OD} With Common-Mode Loading Test Circuit

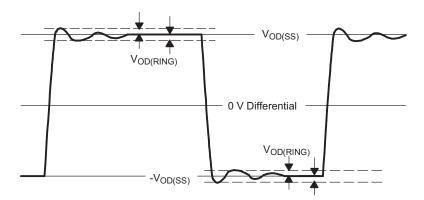
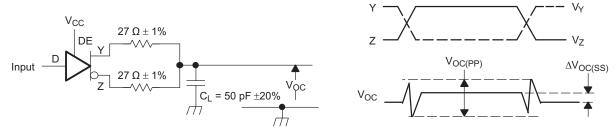


Figure 3. V_{OD(RING)} Waveform and Definitions

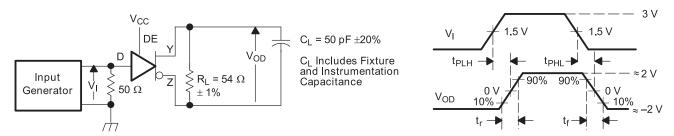
 $V_{\text{OD(RING)}}$ is measured at four points on the output waveform, corresponding to overshoot and undershoot from the $V_{\text{OD(H)}}$ and $V_{\text{OD(L)}}$ steady state values.



Input: PRR = 500 kHz, 50% Duty Cycle, $t_{\rm f}$ < 6 ns, $t_{\rm f}$ < 6 ns, $Z_{\rm O}$ = 50 Ω

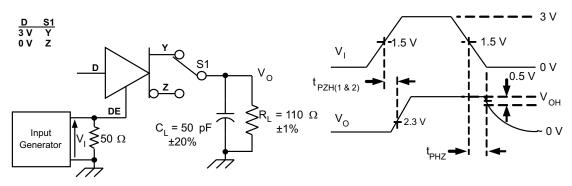
Figure 4. Test Circuit and Definitions for Driver Common-Mode Output Voltage

PARAMETER MEASUREMENT INFORMATION (continued)



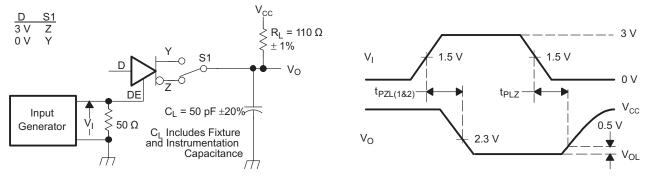
A. Generator: PRR = 500 kHz, 50% Duty Cycle, $t_{\rm r}$ < 6 ns, $t_{\rm f}$ < 6 ns, $Z_{\rm O}$ = 50 Ω

Figure 5. Driver Switching Test Circuit and Voltage Waveforms



- A. Generator: PRR = 500 kHz, 50% Duty Cycle, $t_{\rm r}$ < 6 ns, $t_{\rm f}$ < 6 ns, $Z_{\rm O}$ = 50 Ω
- B. C₁ Includes Fixture and Instrumentation Capacitance

Figure 6. Driver High-Level Output Enable and Disable Time Test Circuit and Voltage Waveforms



A. Generator: PRR = 500 kHz, 50% Duty Cycle, t_r < 6 ns, t_f < 6 ns, Z_O = 50 Ω

Figure 7. Driver Low-Level Output Enable and Disable Time Test Circuit and Voltage Waveforms

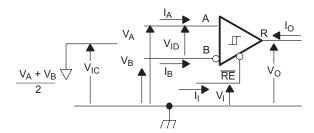
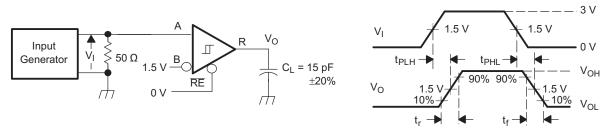


Figure 8. Receiver Voltage and Current Definitions

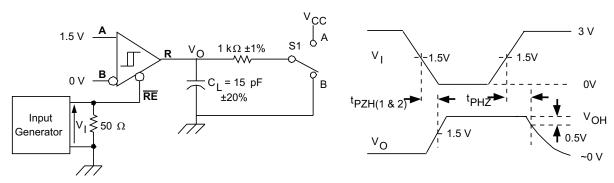


PARAMETER MEASUREMENT INFORMATION (continued)



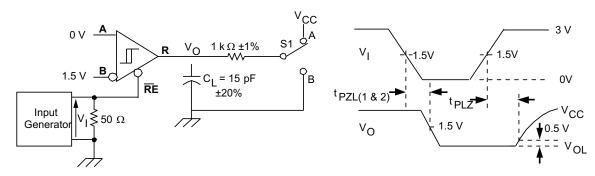
- A. C_L Includes Fixture and Instrumentation Capacitance
- B. Generator: PRR = 500 kHz, 50% Duty Cycle, $t_r < 6$ ns, $t_f < 6$ ns, $Z_O = 50 \Omega$

Figure 9. Receiver Switching Test Circuit and Voltage Waveforms



A. Generator: PRR = 500 kHz, 50% Duty Cycle, t_r < 6 ns, t_f < 6 ns, Z_O = 50 Ω

Figure 10. Receiver High-Level Enable and Disable Time Test Circuit and Voltage Waveforms



A. Generator: PRR = 500 kHz, 50% Duty Cycle, t_r < 6 ns, t_f < 6 ns, Z_O = 50 Ω

Figure 11. Receiver Enable Time From Standby (Driver Disabled)

PARAMETER MEASUREMENT INFORMATION (continued)

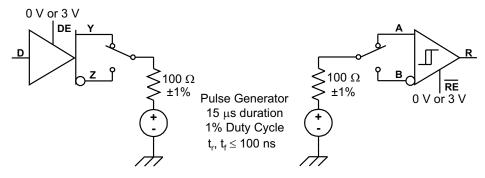


Figure 12. Test Circuit, Transient Over Voltage Test



DEVICE INFORMATION

Low-Power Standby Mode

When both the driver and receiver are disabled (DE low and RE high), the device is in standby mode. If the enable inputs are in this state for less than 60 ns, the device does not enter standby mode. This guards against inadvertently entering standby mode during driver/receiver enabling. Only when the enable inputs are held in this state for 300 ns or more, the device is assured to be in standby mode. In this low-power standby mode, most internal circuitry is powered down, and the supply current is typically less than 1 nA. When either the driver or the receiver is re-enabled, the internal circuitry becomes active.

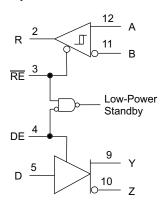


Figure 13. Low-Power Standby Logic Diagram

If only the driver is re-enabled (DE transitions to high), the driver outputs are driven according to the D input after the enable times given by t_{PZH2} and t_{PZL2} in the driver switching characteristics. If the D input is open when the driver is enabled, the driver outputs defaults to A high and B low, in accordance with the driver fail-safe feature.

If only the receiver is re-enabled (\overline{RE} transitions to low), the receiver output is driven according to the state of the bus inputs (A and B) after the enable times given by t_{PZH2} and t_{PZL2} in the receiver switching characteristics. If there is no valid state on the bus, the receiver responds as described in the fail-safe operation section.

If both the receiver and driver are re-enabled simultaneously, the receiver output is driven according to the state of the bus inputs (A and B) and the driver output is driven according to the D input. Note that the state of the active driver affects the inputs to the receiver. Therefore, the receiver outputs are valid as soon as the driver outputs are valid.

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DEVICE INFORMATION (continued)

FUNCTION TABLES

SN65HVD33, SN65HVD34, SN65HVD35, SN65HVD38, SN65HVD39 DRIVER⁽¹⁾

IN	IPUTS	OUTPUTS		
D	DE	Y	Z	
Н	Н	Н	L	
L	Н	L	Н	
Х	L or open	Z	Z	
Open	Н	L	Н	

(1) H = high level, L = low level, Z = high impedance, X = irrelevant

Table 1. SN65HVD33, SN65HVD34, SN65HVD35, SN65HVD38, SN65HVD39 RECEIVERSLLS6651132⁽¹⁾

DIFFERENTIAL INPUTS $V_{ID} = V_{(A)} - V_{(B)}$	ENABLE RE	OUTPUT R
$V_{ID} \le -0.2 \text{ V}$	L	L
$-0.2 \text{ V} < \text{V}_{\text{ID}} < -0.02 \text{ V}$	L	?
-0.02 V ≤ V _{ID}	L	Н
X	H or open	Z
Open circuit	L	Н
Idle circuit	L	Н
Short circuit, $V_{(A)} = V_{(B)}$	L	Н

(1) H = high level, L = low level, Z = high impedance, X = irrelevant, ? = indeterminate

SN65HVD30, SN65HVD31, SN65HVD32, SN65HVD36, SN65HVD37 DRIVER⁽¹⁾

INPUT	OUTPUTS					
D	Y	Z				
Н	Н	L				
L	L	Н				
Open	L	Н				

(1) H = high level, L = low level

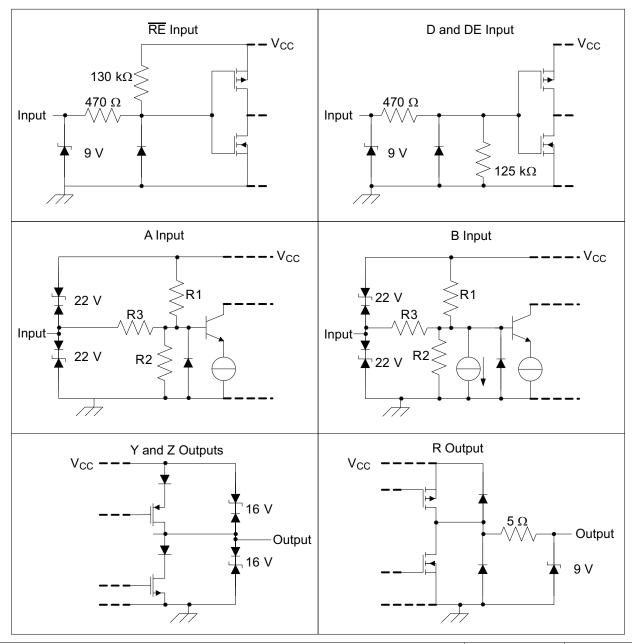
SN65HVD30, SN65HVD31, SN65HVD32, SN65HVD36, SN65HVD37 RECEIVER (1)

DIFFERENTIAL INPUTS $V_{ID} = V_{(A)} - V_{(B)}$	OUTPUT R
V _{ID} ≤ -0.15 V	L
-0.15 V < V _{ID} < -0.02 V	?
-0.02 V ≤ V _{ID}	Н
Open circuit	Н
Idle circuit	Н
Short circuit, V _(A) = V _(B)	Н

(1) H = high level, L = low level, ? = indeterminate

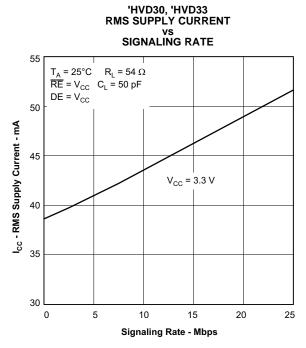


EQUIVALENT INPUT AND OUTPUT SCHEMATIC DIAGRAMS



	R1/R2	R3
SN65HVD30, SN65HVD33, SN65HVD36, SN65HVD38	9 kΩ	45 kΩ
SN65HVD31, SN65HVD32, SN65HVD34, SN65HVD35 SN65HVD37, SN65HVD38, SN65HVD39	36 kΩ	180 kΩ

TYPICAL CHARACTERISTICS



'HVD31, 'HVD34 RMS SUPPLY CURRENT vs SIGNALING RATE 60 $T_A = 25^{\circ}C$ $R_L = 54 \Omega$ $\overline{RE} = V_{CC}$ $C_L = 50 \text{ pF}$ DE = V_{CC} I_{CC} - RMS Supply Current - mA 50 45 $V_{CC} = 3.3 \text{ V}$ 40 35 30 0 1 3 5 Signaling Rate - Mbps

Figure 14.

Figure 15.

'HVD32, 'HVD35 RMS SUPPLY CURRENT VS SIGNALING RATE

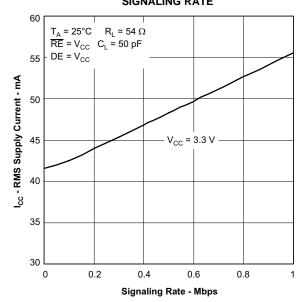


Figure 16.



TYPICAL CHARACTERISTICS (continued)

40

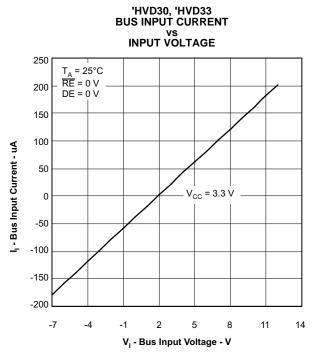


Figure 17.

DRIVER LOW-LEVEL OUTPUT CURRENT

vs LOW-LEVEL OUTPUT VOLTAGE 0.14 V_{CC} = 3.3 V DE = V_{CC} 0.12 D = 0 VIoL - Low-level Output Current - A 0.1 0.08 0.06 0.04 0.02 0 -0.02 2.5 0 0.5 2 3 3.5 V_{OL} - Low-Level Output Voltage - V

Figure 19.

'HVD31, 'HVD32, 'HVD34, 'HVD35 BUS INPUT CURRENT VS INPUT VOLTAGE T_A = 25°C RE = 0 V DE = 0 V

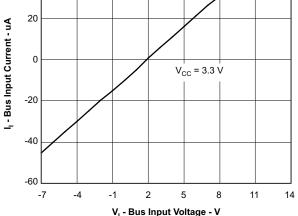


Figure 18.

DRIVER HIGH-LEVEL OUTPUT CURRENT VS HIGH-LEVEL OUTPUT VOLTAGE

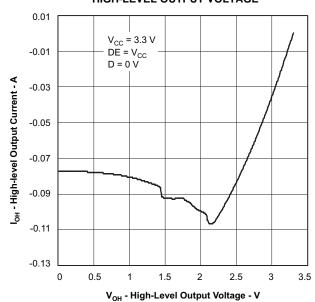


Figure 20.

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TYPICAL CHARACTERISTICS (continued)

DRIVER DIFFERENTIAL OUTPUT VOLTAGE vs FREE-AIR TEMPERATURE

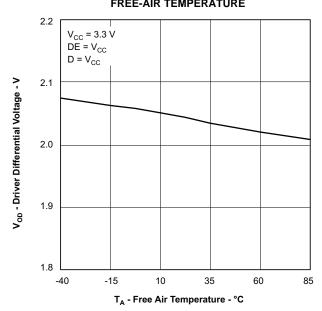


Figure 21.

DRIVER OUTPUT CURRENT VS SUPPLY VOLTAGE

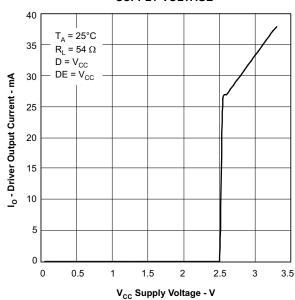


Figure 22.

22-Sep-2008

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
SN65HVD30MDREP	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65HVD30MDREPG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65HVD33MDREP	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65HVD33MDREPG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
V62/06634-01XE	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
V62/06634-04YE	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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OTHER QUALIFIED VERSIONS OF SN65HVD30-EP, SN65HVD33-EP:

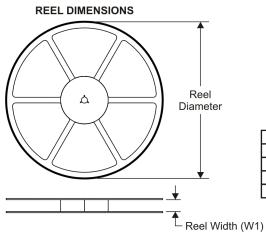
• Catalog: SN65HVD30, SN65HVD33

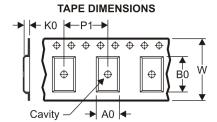
NOTE: Qualified Version Definitions:

Catalog - TI's standard catalog product

5-Nov-2008

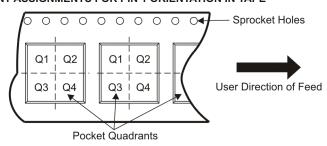
TAPE AND REEL INFORMATION





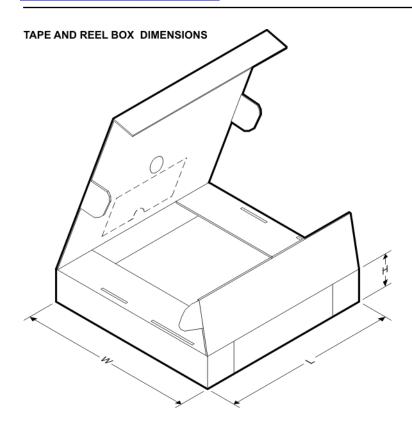
	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65HVD30MDREP	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN65HVD33MDREP	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1

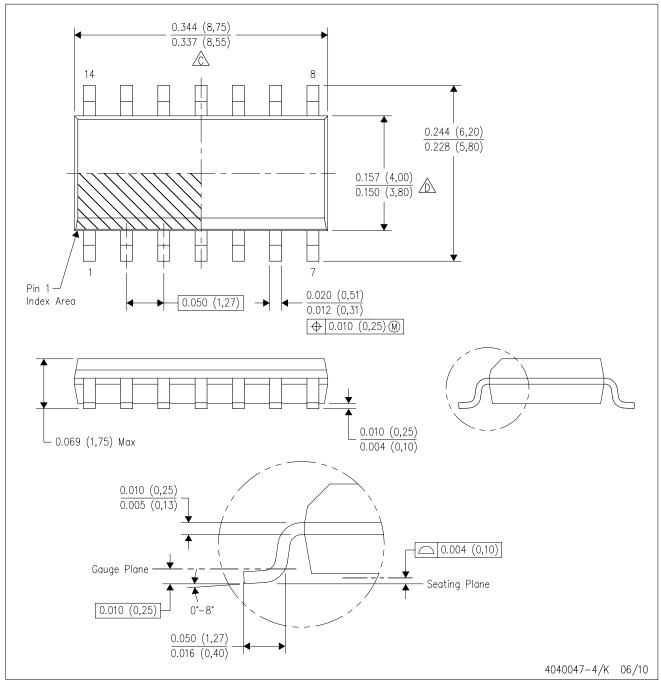


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65HVD30MDREP	SOIC	D	8	2500	346.0	346.0	29.0
SN65HVD33MDREP	SOIC	D	14	2500	333.2	345.9	28.6

D (R-PDSO-G14)

PLASTIC SMALL-OUTLINE PACKAGE

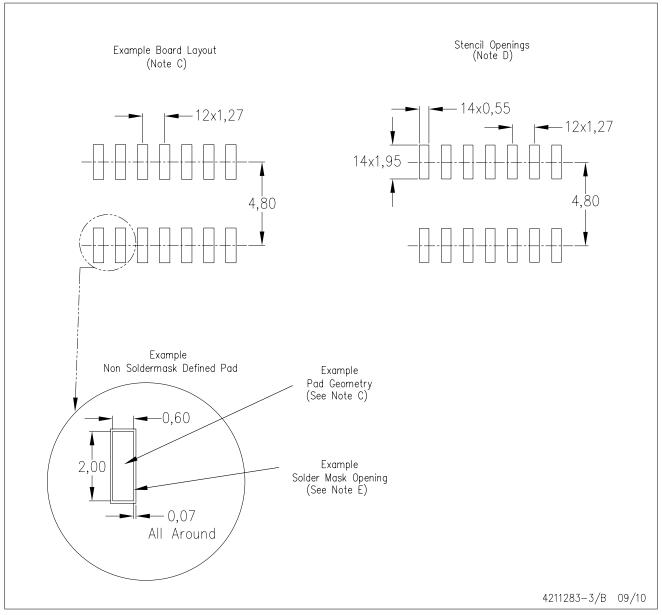


- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 (0,15) per end.
- Body width does not include interlead flash. Interlead flash shall not exceed .017 (0,43) per side.
- E. Reference JEDEC MS-012 variation AB.



D (R-PDSO-G14)

PLASTIC SMALL OUTLINE

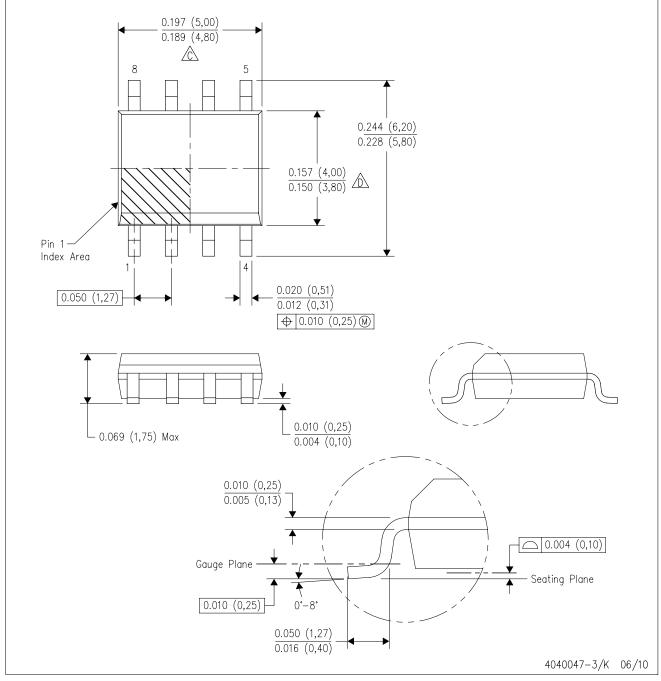


- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



D (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE

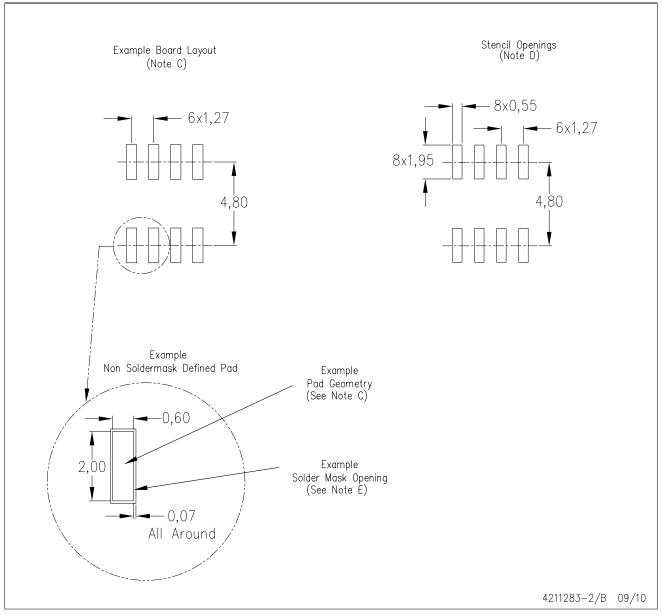


- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 (0,15) per end.
- Body width does not include interlead flash. Interlead flash shall not exceed .017 (0,43) per side.
- E. Reference JEDEC MS-012 variation AA.



D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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